

MMBT3904L

200 mA, 40 V NPN Bipolar Junction Transistor

Product Overview

For complete documentation, see the data sheet.

This 200 mA, 40 V NPN Bipolar Junction Transistor is designed for use in linear and switching applications. The device is housed in the SOT-23 package, which is designed for lower power surface mount applications.

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Part Electrical Specifications																					
Product	Status	Compilance	Po lar ity	Ty	V _C E(s at) M ax (V	I _C Co nt. (A	V _C EO Mi n (V	V _C BO (V	V _E BO (V	V _B E(s at) (V	V _B E(o n) (V	h _F E Mi n	h _F E M ax	f _T Mi n (M Hz)	P _T M M ax (W	Pa ck ag e Ty pe	Ca se O utl in e	M SL Ty pe	M SL Te m p (° C)	Co nt ai ne r Ty pe	Co nt ai ne r Qt y.
MMBT3904LT1 G	Active	(1) (2)	N P N	Ge ne ral Pu rp os e	0. 3	0. 2	40	60	6	0. 95	-	10 0	30	30	0. 22 5	S O T-23 (T O-23 6) 2. 90 x1. 30 x1. 00 P	31 8. P DF	1	26 0	RE EL	30
MMBT3904LT3 G	Active	(†) 20	N P N	Ge ne ral Pu rp os e	0. 3	0. 2	40	60	6	0. 95	-	10 0	30	30	0. 22 5	S O T-23 (T O-23 6) 2. 90 x1. 30 x1. 00 ,1. 90 P	31 8. P DF	1	26 0	RE EL	10 00 0
SMMBT3904LT 1G	Active	# 20 A P	N P N	Ge ne ral Pu rp os e	0. 3	0. 2	40	60	6	0. 95	-	10 0	30	30 0	0. 22 5	S OT- 23 (T O- 23 6) 2. 90 x1. 30 x1. 00 1. 90 P	31 8. P DF	1	26 0	RE EL	30 00
SMMBT3904LT 3G	Active	# ²⁰	N P N	Ge ne ral Pu rp os e	0. 3	0. 2	40	60	6	0. 95	-	10 0	30 0	30 0	0. 22 5	S O T-23 (T O-23 6) 2. 90 x1. 30 x1. 00 ,1. 90 P	31 8. P DF	1	26 0	RE EL	10 00 0